



12815 NE 124th St STE#D, Kirkland, WA-98034

AS4C256M16D3LC-10BCN vs AS4C256M16D3LD-10BCN Comparison

Part Number & result Parameter	AS4C256M16D3LC-10BCN	AS4C256M16D3LD-10BCN	Comparison Result
Product Description	DDR3L SDRAM	DDR3L SDRAM	Same
Capacity	4Gb (256M x 16)	4Gb (256M x 16)	Same
Memory Organization	32Meg, x16bits, x8 banks	32Mwords, x16bits, x8 banks	Same
Operating Power Supply	VDD/Q = +1.35V (1.283V to 1.45V) Backward compatible +1.5V ±0.075V	VDD/Q = +1.35V (1.283V to 1.45V) Backward compatible +1.5V ±0.075V	Same
Operating Temperature	Commercial (0°C to 95°C)	Commercial (0°C to 95°C)	Same
Clock Frequency (Max)	933MHz	933MHz	Same
Data Rate (Max)	1866 Mbps	1866 Mbps	Same
CAS Latency	13	13	Same
tRCD & tRP (ns)	13.91	13.91	Same
Average Refresh Period	7.8us (<85C), 3.9us at 85C~95C	7.8us (<85C), 3.9us at 85C~95C	Same
I/O Capacitance	2.1pf	2.1pf	Same
Pin to Pin Compatible	Pin to Pin Compatible		
AC/DC Characteristics	Same	Same	Meet JEDEC
IDD Specification			
IDD Spec conditions	0C to 95C	0C to 95C	Same
I_{DD0} (mA)	59	130	RevC better
I_{DD1} (mA)	84	160	RevC better
I_{DD2P0} (mA)	8	52	RevC better
I_{DD2P1} (mA)	16	85	RevC better
I_{DD2N} (mA)	26	90	RevC better
I_{DD2Q} (mA)	26	90	RevC better
I_{DD3P} (mA)	28	90	RevC better
I_{DD3N} (mA)	40	115	RevC better
I_{DD4R} (mA)	165	240	RevC better
I_{DD4W} (mA)	165	240	RevC better
I_{DD5B} (mA)	242	207	RevD better
I_{DD6} (mA)	12	45	RevC better
I_{DD7} (mA)	200	300	RevC better
I_{DD8} (mA)	10	30	RevC better
Package 96b FBGA	(7.5mm x 13.5mm x 1.2mm) Ball Array : 12mm x 6.4mm x 0.8mm	(7.5mm x 13.0mm x 1.0mm) Ball Array : 12mm x 6.4mm x 0.8mm	Comparable
Package Material	Pb and Halogen Free	Pb and Halogen Free	Same